Silicon NPN Power Transistors 2SD798

DESCRIPTION

·With TO-220 package
·High voltage
·DARLINGTON

APPLICATIONS

·With switching and igniter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

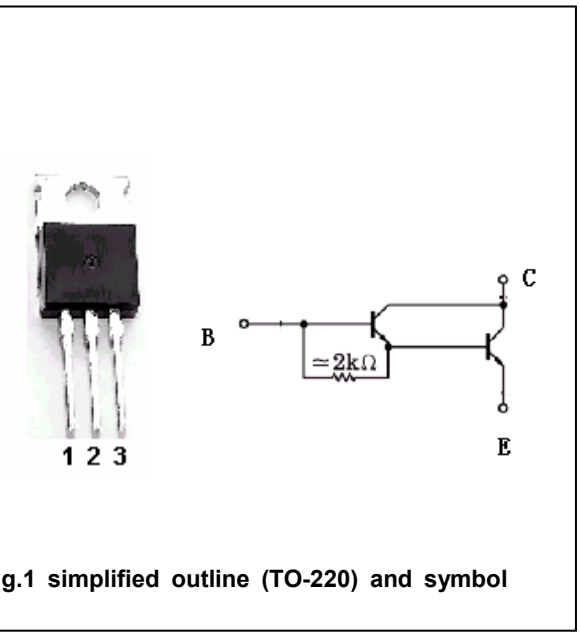

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.5A ;L=40mH	300			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A ;I_B=0.04A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A ;I_B=0.04A			2.5	V
I_{CBO}	Collector cut-off current	V_{CB}=600V; I_E=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.5	mA
h_{FE-1}	DC current gain	I_C=2A ; V_{CE}=2V	1500			
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=2V	200			
C_{OB}	Collector output capacitance	f=1MHz;V_{CB}=50V		35		pF
Switching times						
t_{on}	Turn-on time	I_{B1}=-I_{B2}=0.04A V_{CC}≈100V,R_L=25Ω		1		μs
t_{stg}	Storage time			8		μs
t_f	Fall time			5		μs

PACKAGE OUTLINE

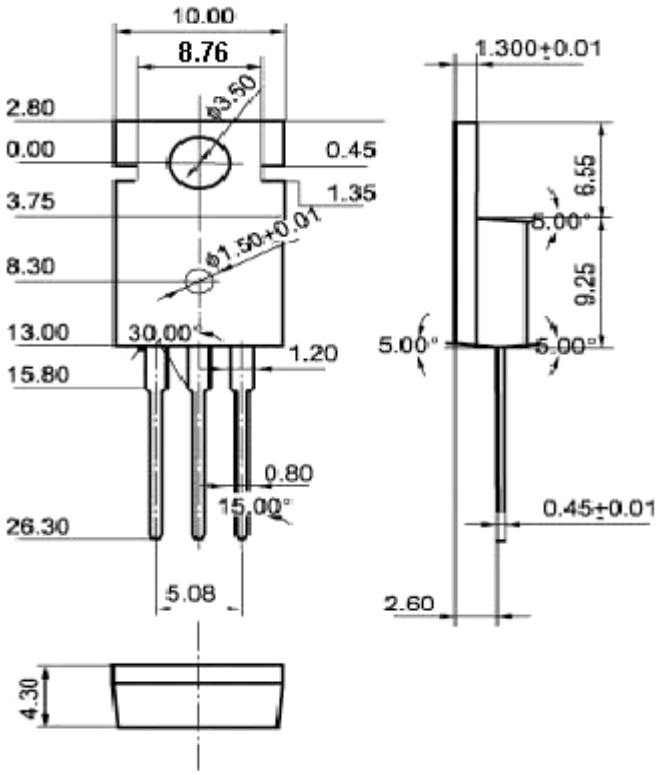

Fig.2 Outline dimensions